**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package. This very sensitive gate "series D" triac is intended for interfacing with low power drivers including microcontrollers.

#### 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate
- Triggering in all four quadrants

## 3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- General purpose switching and phase control

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	-	12.5	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	1	A
Static charac	teristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;	-	-	7	mA
		T <sub>j</sub> = 25 °C; <u>Fig. 7</u>				

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate		G sym051
3	T1	main terminal 1		, and the second
			TO-92 (SOT54)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package	kage				
	Name	Description	Version			
BT131-800D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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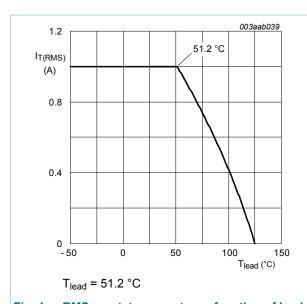
# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	1	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	12.5	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	13.7	Α
I <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1.5 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+	-	50	A/µs
		$I_T$ = 1.5 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G-	-	50	A/µs
		$I_T$ = 1.5 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G-	-	50	A/µs
		$I_T$ = 1.5 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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f = 50 Hz; T<sub>lead</sub> = 51.2 °C

Fig. 1. RMS on-state current as a function of lead temperature; maximum values

Fig. 2. RMS on-state current as a function of surge duration; maximum values

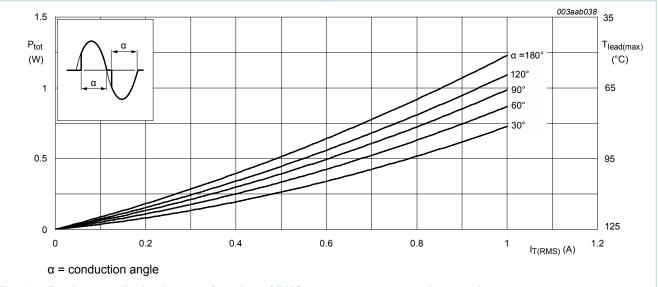
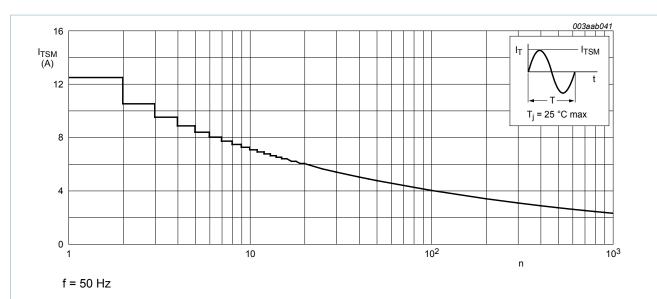


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

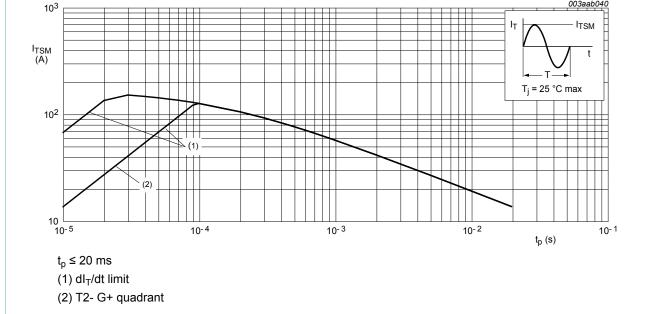
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Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum



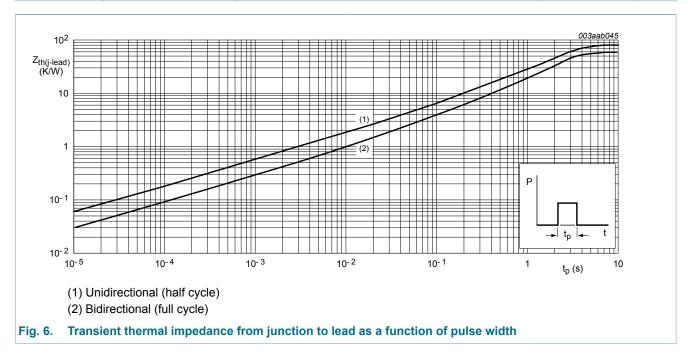
Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values Fig. 5.

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
tity icad)	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted: lead length 4 mm	-	150	-	K/W



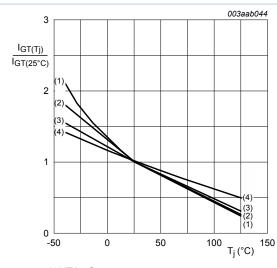
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## 9. Characteristics

Table 6 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		<u> </u>			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	7	mA
I <sub>L</sub> latching current	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic o	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $R_{GT1}$ = 1 k $\Omega$ ; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform	20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/$ $dt$ = 0.5 A/ms; $I_T$ = 1 A; gate open circuit	3	-	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 1.5 A; $V_D$ = 800 V; $I_G$ = 0.1 A; $dI_{G}/dt$ = 5 A/ $\mu$ s	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

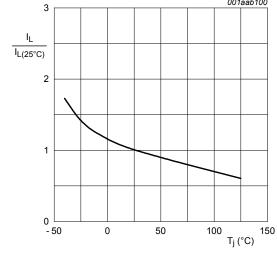


Fig. 8. Normalized latching current as a function of junction temperature

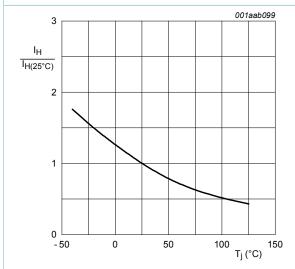
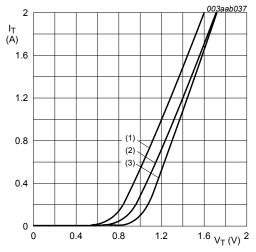


Fig. 9. Normalized holding current as a function of junction temperature



- $V_0 = 0.92 \text{ V}; R_s = 0.4 \Omega$
- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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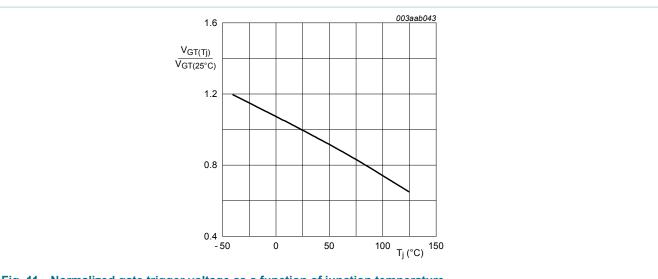


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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# 10. Package outline

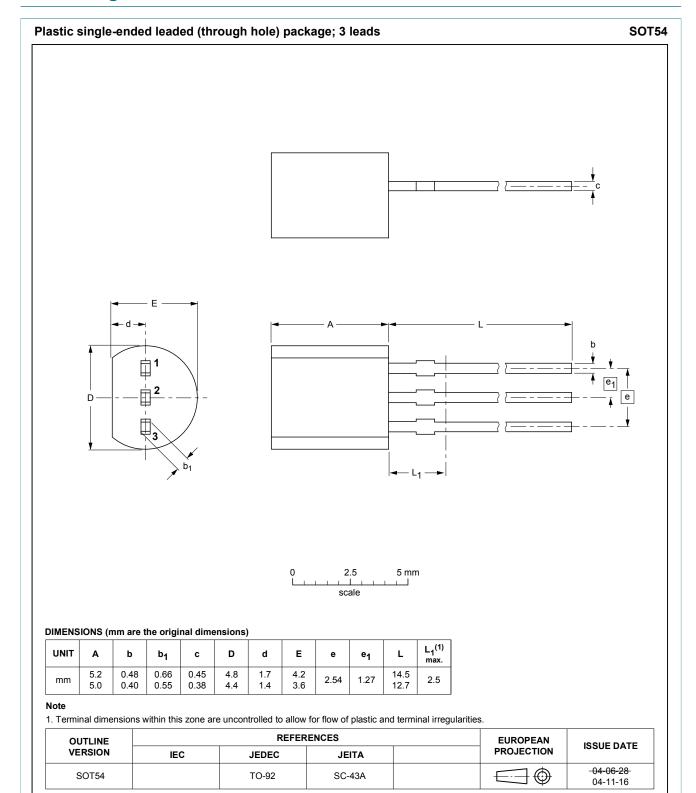


Fig. 12. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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